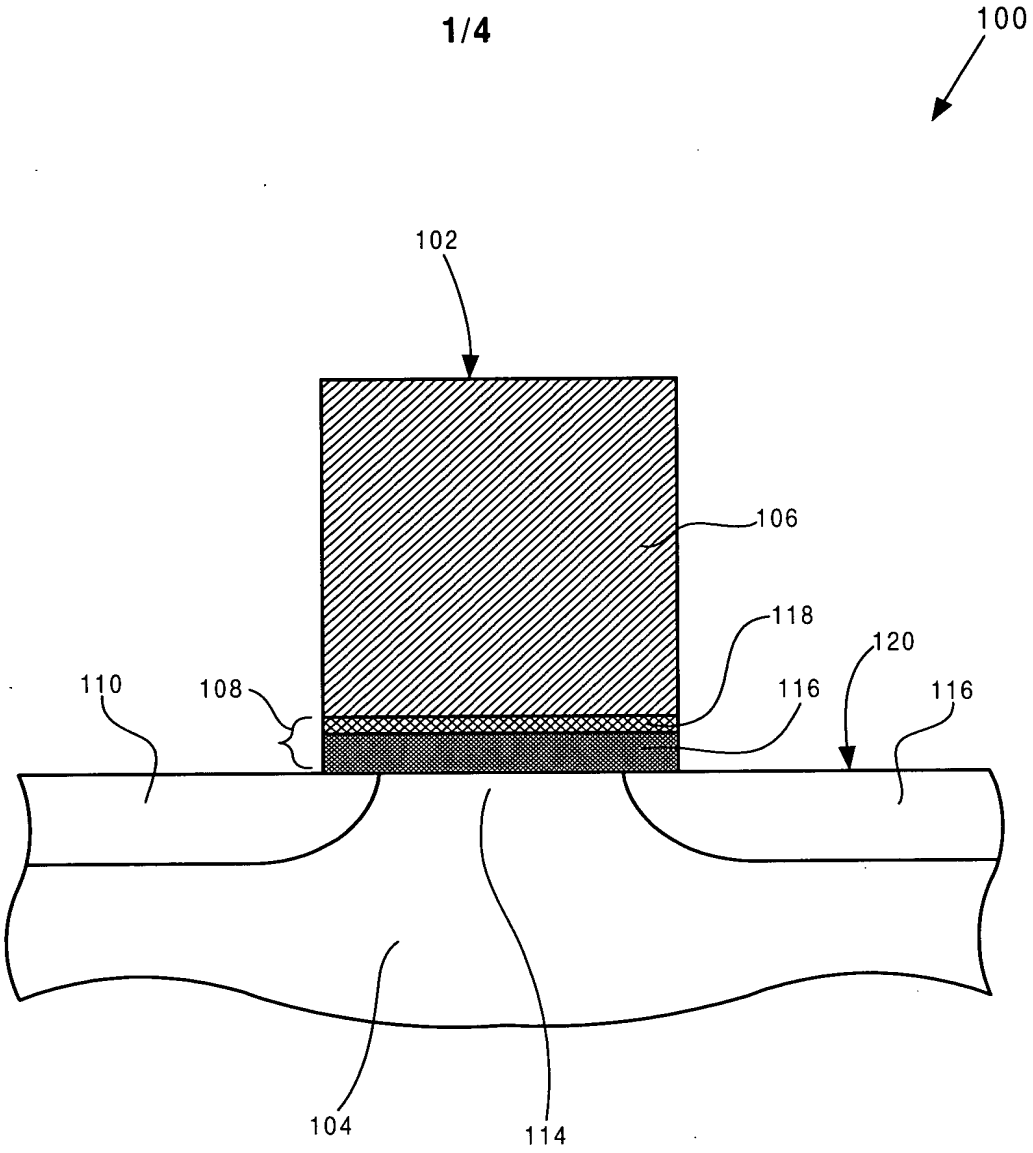

Fig. 1

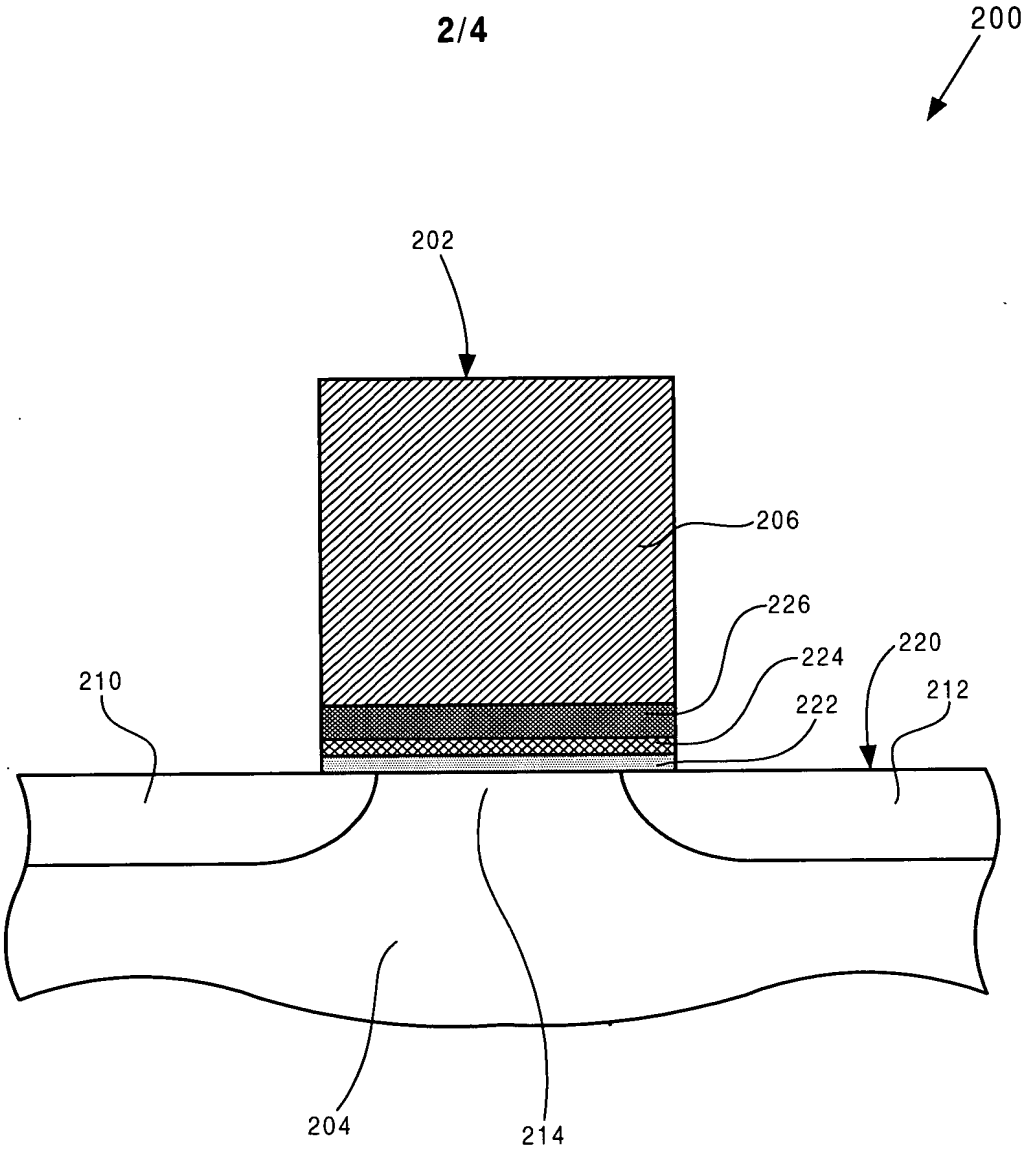

Fig. 2

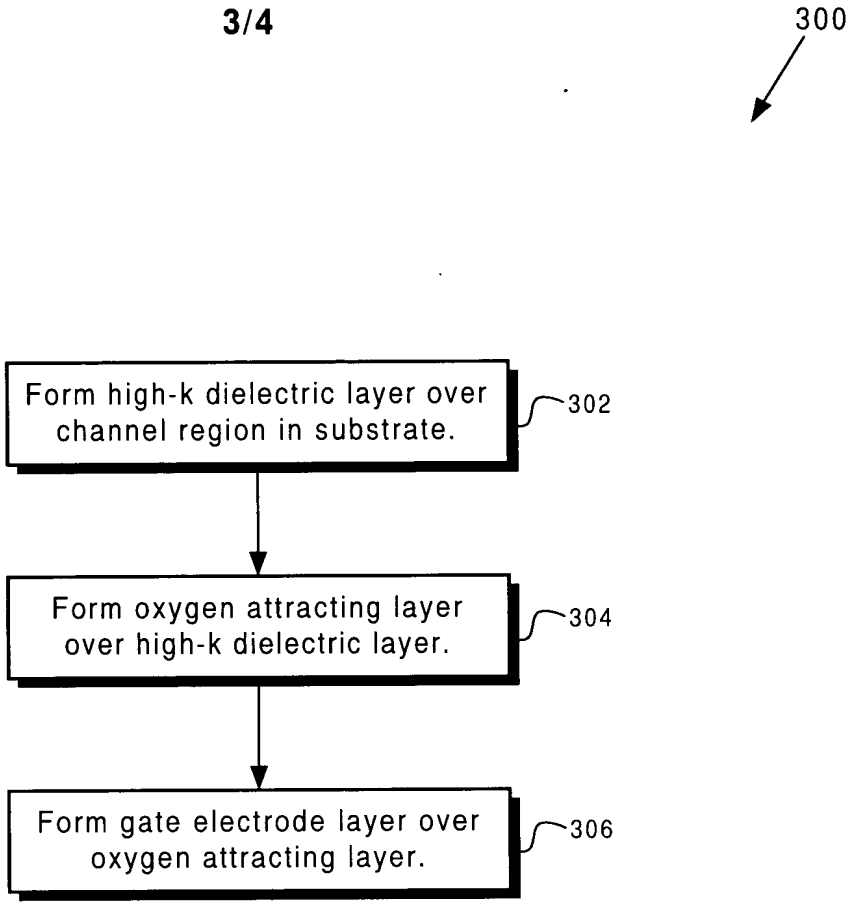
300
Form high-k dielectric layer over channel region in substrate.
302
Form oxygen attracting layer over high-k dielectric layer.
304
Form gate electrode layer over oxygen attracting layer.
306

Fig. 3

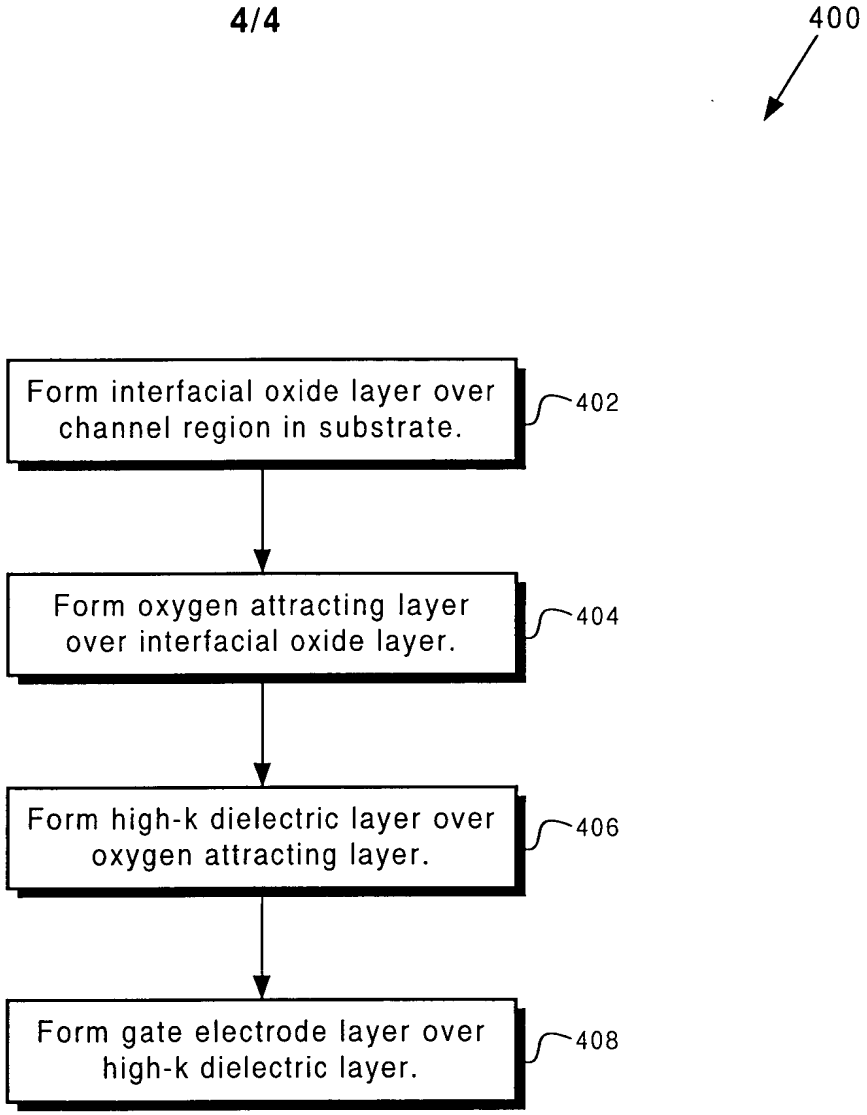
400
Form interfacial oxide layer over channel region in substrate.
402
Form oxygen attracting layer over interfacial oxide layer.
404
Form high-k dielectric layer over oxygen attracting layer.
406
Form gate electrode layer over high-k dielectric layer.
408

Fig. 4